



Attorney Docket SEL 154

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In Re Application of)
Shunpei YAMAZAKI)
Serial No.: 09/479,262)
Filed: January 5, 2000)
Art Unit: 2815)
Examiner: E. Wojciechowicz)
For: Semiconductor Device and)
Method of Manufacturing)
the Same)

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Commissioner for Patents, Washington, D.C. 20231 on October 23, 2001

Signature

Name: Bobbi Wilson

6/A

1-16-02

T. Flower

AMENDMENT

Commissioner for Patents
Washington, D.C. 20231

In the Claims:

Please amend claims 1-12, 14-18, and 20-24 to read as follows:

1. (Amended) A semiconductor device comprising:
a gate electrode formed on an insulting surface;
a gate insulating film comprising at least a single layer on said gate electrode; and
a source region, a drain region, and a channel formation region formed between said source region and said drain region, the respective regions begin in contact with said gate insulating film;

A1

RECEIVED
JAN 14 2002
TECHNOLOGY CENTER 2800